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Ko

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(54) **METHOD OF FABRICATING
ELECTROLUMINESCENT DISPLAY**

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(51) **Int. Cl.**

H01L 51/40 (2006.01)
H01L 21/338 (2006.01)
H01L 21/00 (2006.01)

(52) **U.S. Cl.** **438/99; 438/179; 438/82;**
257/E21.123

(58) **Field of Classification Search** **438/99,**
438/179, 82; 257/E21.123
See application file for complete search history.

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Primary Examiner—Scott B. Geyer

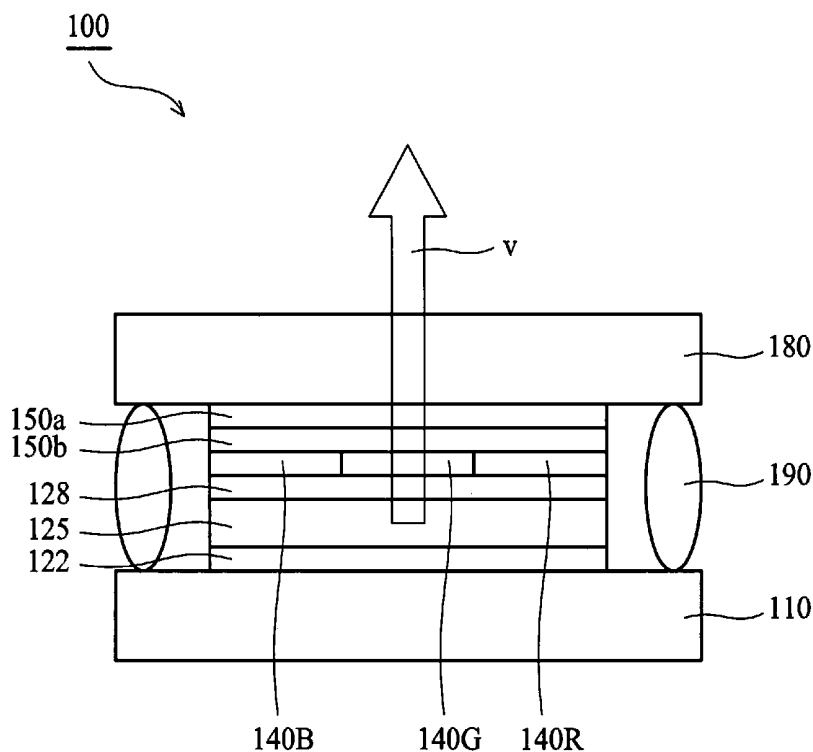
Assistant Examiner—Seahvosh J Nikmanesh

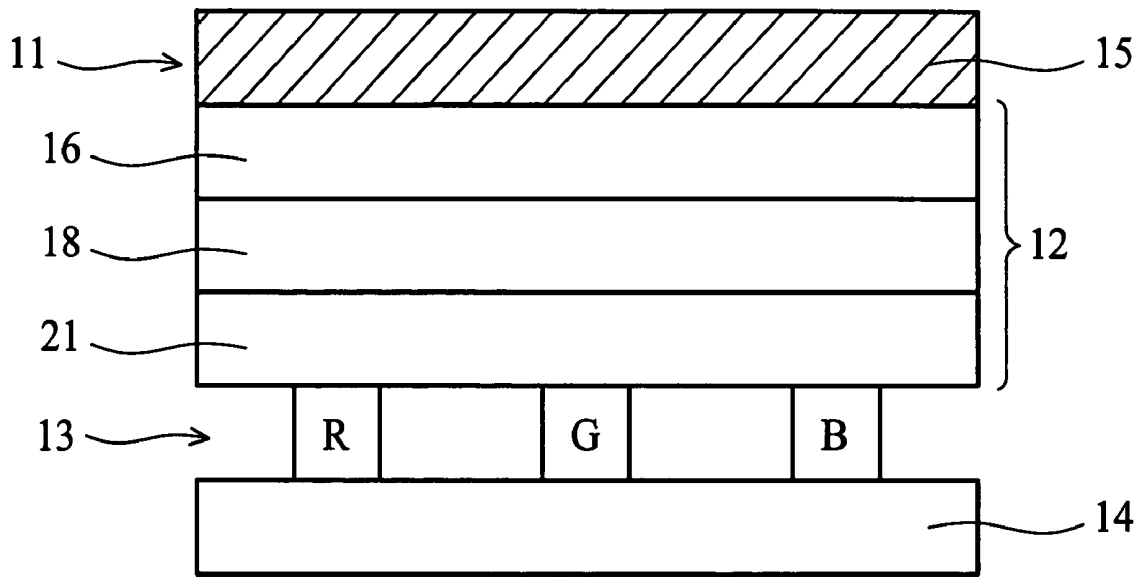
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(57) **ABSTRACT**

A method for fabrication organic light emitting diode (OLED) displays. A white light OLED element is formed on the first substrate. A micro-cavity layer is formed on a second substrate. A color filter is formed on the micro-cavity layer. The first and the second substrates are assembled, wherein the light of white OLED element passes through the color filter and the micro-cavity layer.

9 Claims, 5 Drawing Sheets





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FIG. 1 (RELATED ART)

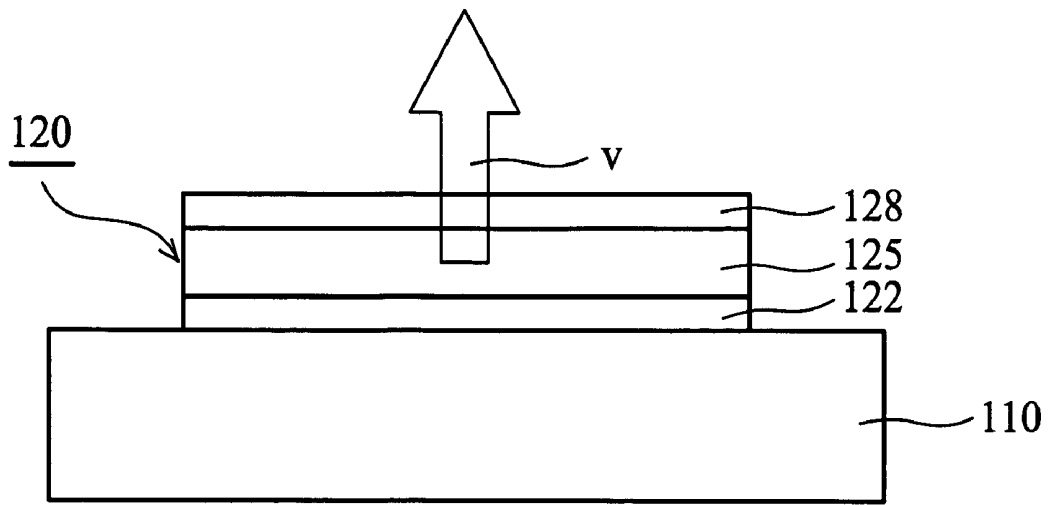


FIG. 2A

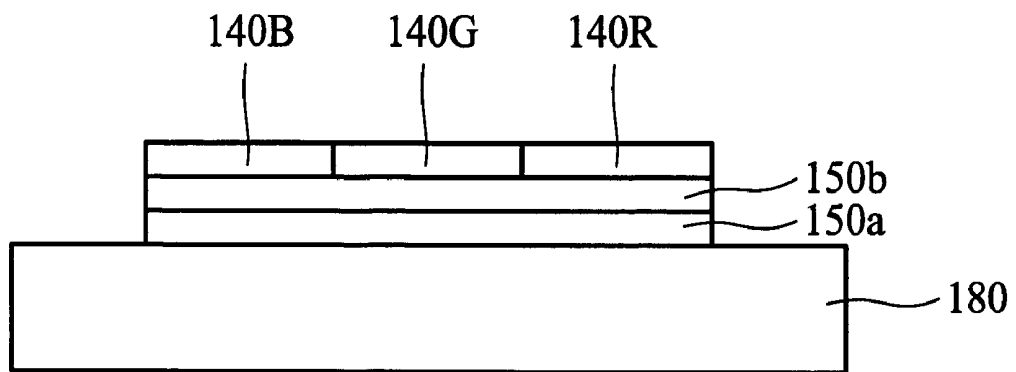


FIG. 2B

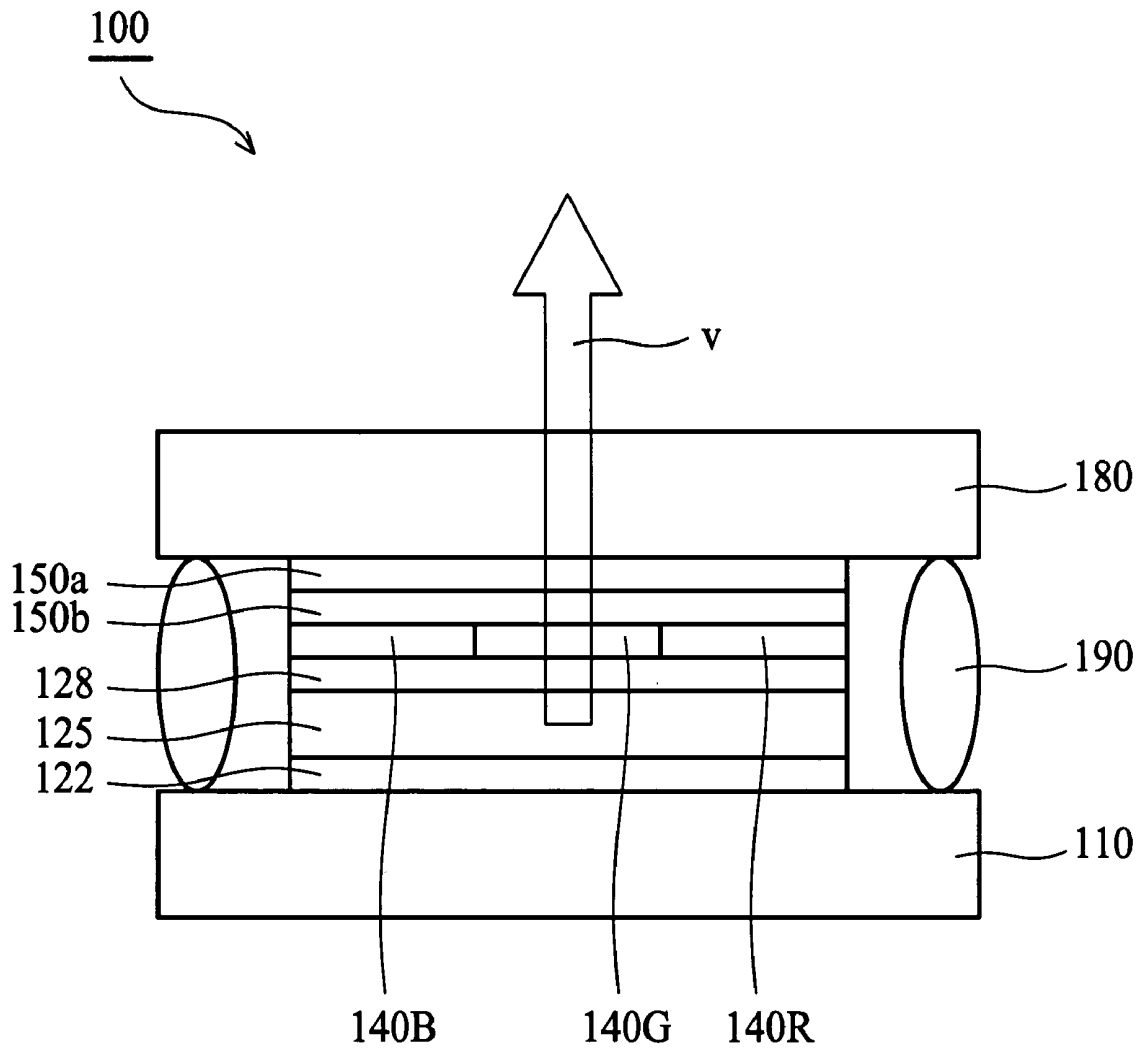


FIG. 2C

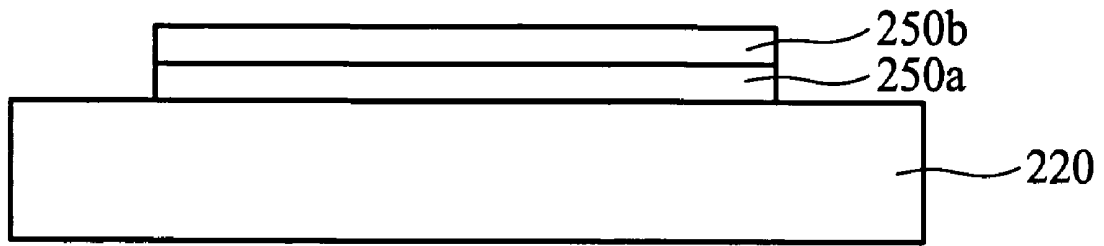


FIG. 3A

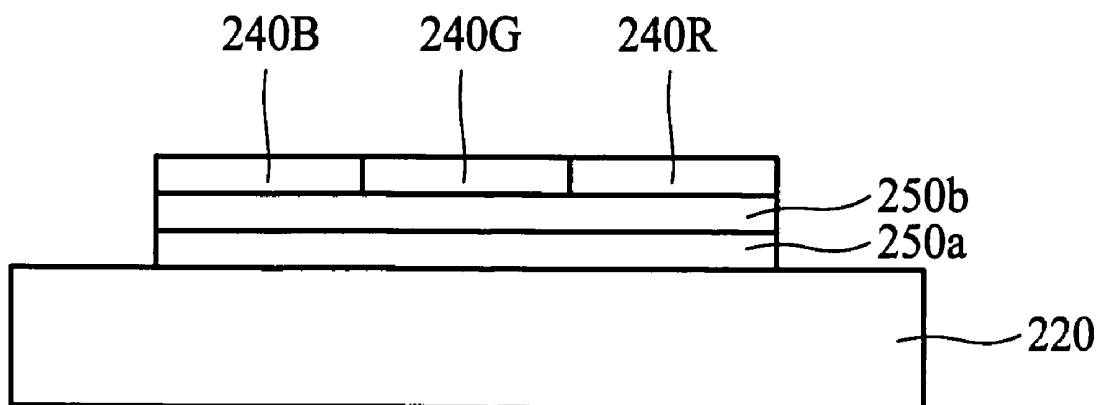


FIG. 3B

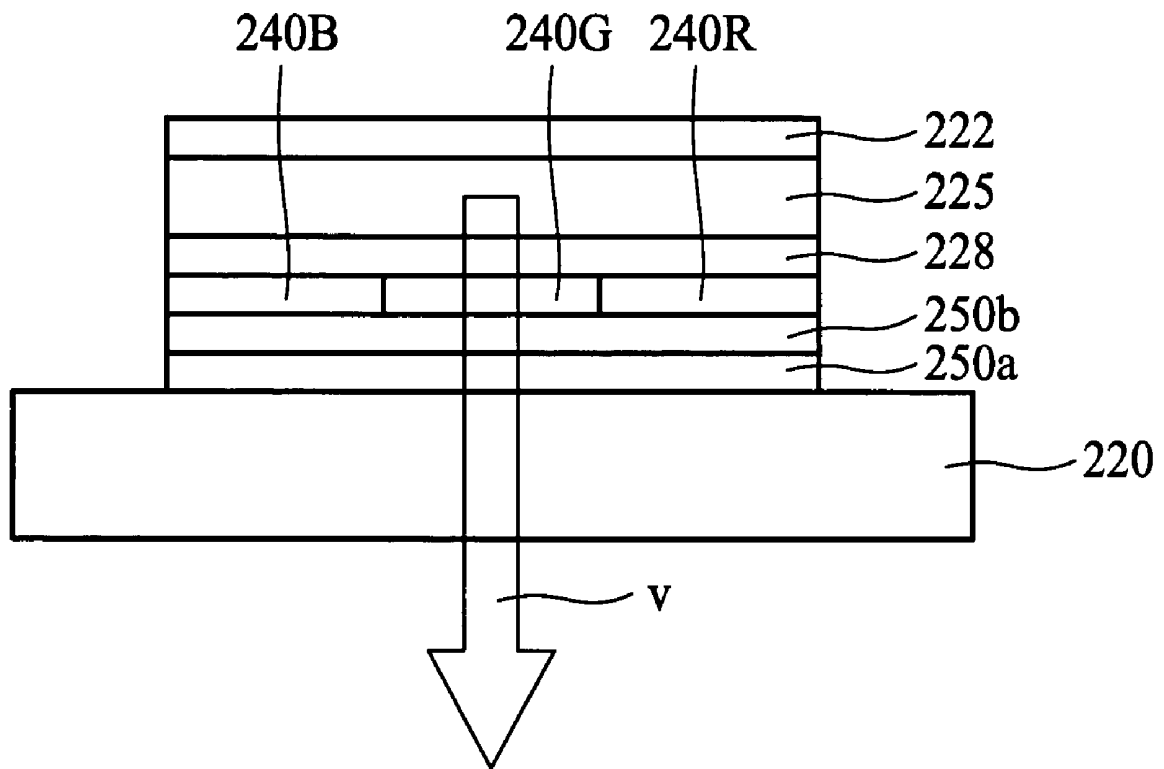


FIG. 3C

METHOD OF FABRICATING ELECTROLUMINESCENT DISPLAY

BACKGROUND

The invention relates to methods of fabricating electroluminescent displays, and more particularly, to methods of fabricating organic light emitting diode (OLED) displays with multi-mode micro-cavity layers.

Among flat panel displays, organic light emitting diode (OLED) displays exhibit characteristics of self-emission, high brightness, wide viewing angle, high response, simple fabrication process, low power consumption, and good outdoor reliability, and are therefore widely applied in portable computers, notebooks, mobile phones, and personal digital assistants (PDAs).

To achieve full color display, a conventional OLED display comprises OLED elements having red, green, and blue pixels, separately formed on an active matrix substrate. Conventional fabrication methods for OLED displays require precision alignment and a shadow mask process, thus the fabrication process is complicated.

White light OLED displays with color filter thereon are proposed to simplify fabrication. U.S. Pat. No. 6,133,692, the entirety of which is hereby incorporated by reference, discloses a method of fabricating white light OLED displays. FIG. 1 is a cross section of a conventional white light OLED display. A white light OLED display 10 comprises an organic light emitting diode element 11, a multi-mode micro-cavity layer 12, and a color filter 13, disposed on a transparent substrate 14. The organic light emitting diode element 11 comprises an upper electrode 15, at least one light emitting layer 16, and a lower electrode 18. A mirror stack structure 21 is interposed between the lower substrate 18 and color filter 13.

Since the light from the conventional white light OLED display comprises a broadband spectrum, even after passing through a color filter, each red, green, and blue light is still broadband. The colors of the white light OLED display are less saturated than in a conventional tri-color OLED display. Moreover, a color filter of a conventional white light OLED display is organic, and the multi-mode micro-cavity layer is metal or an inorganic material. From a processing point of view, forming an organic color filter at low temperature prior to a micro-cavity layer at high temperature of may complicate the fabrication process, reducing the process window and increasing production costs.

SUMMARY

Accordingly, the invention provides an organic light emitting diode (OLED) display with a multi-mode micro-cavity layer, enhancing color saturation and process compatibility.

The invention also provides a method for fabricating an organic light emitting diode (OLED) display. A white light OLED element is formed on a first substrate. At least one micro-cavity layer is formed on a second substrate. A color filter is formed on the at least one micro-cavity layer. The first substrate and the second substrate are assembled opposing each other, whereby a white light emitted by the OLED element sequentially passes through the color filter and the micro-cavity layer.

The invention further provides a method for fabricating an organic light emitting diode (OLED) display. At least one micro-cavity layer is formed on a substrate. A color filter is formed on the at least one micro-cavity layer. A white light OLED element is formed on the color filter.

DESCRIPTION OF THE DRAWINGS

The invention can be more fully understood by reading the subsequent detailed description in conjunction with the examples and references made to the accompanying drawings, wherein

FIG. 1 is a cross section of a conventional white light OLED display;

FIGS. 2A-2C are cross sections of an embodiment of a method of fabricating an organic light emitting diode (OLED) device; and

FIGS. 3A-3C are cross sections of another embodiment of a method of fabricating an organic light emitting diode (OLED) device.

DETAILED DESCRIPTION

FIGS. 2A-2C are cross sections of an embodiment of a method of fabricating an organic light emitting diode (OLED) device. Referring to FIG. 2A, a white light organic light emitting diode (OLED) element 120 is formed on a first substrate 110, comprising a transparent substrate such as glass or a thin film transistor (TFT) array substrate. The white OLED element 120 comprises a first electrode 122, an organic light emitting structure 125, and a second electrode 128. The white OLED element 120, preferably a top emission OLED, emitting light toward an observer in the direction indicated by arrow v, emits spectrums comprising red (R), green (G), and blue (B) colors.

The first electrode 122 such as an anode is an electrode for hole injection, preferably comprising indium tin oxide (ITO), indium zinc oxide (IZO), silver (Ag), or other high work function material.

The organic light emitting structure 125 preferably comprises an electron transport layer (ETL), an organic light emitting layer, and a hole transport layer (HTL). The organic light emitting layer 125 can be oligomer, polymer, or organic metallic complexes.

A second electrode 128 such as cathode is a metal electrode for electron injection, preferably comprising calcium (Ca), magnesium (Mg), aluminum (Al), or other low work function material. Alternatively, the second electrode may comprise Ca—Al dual layer, Mg—Ag dual layer, LiF—Al dual layer or Mg—Ag alloy or stacks comprising ITO layer and electrodes thereof.

Referring to FIG. 2B, micro-cavity layers 150a and 150b are formed on the second substrate 180. Micro-cavity layers 150a and 150b may comprise one or more materials with different refraction indices, such as oxides, nitrides, semiconductors, metals, or combination thereof. For example, oxides comprise silicon oxide (SiO₂), titanium oxide (TiO₂), tantalum oxide (Ta₂O₅), tin oxide (SnO₂), indium tin oxide (ITO), indium zinc oxide (IZO), or zinc oxide (ZnO). Nitrides may comprise silicon nitride (Si₃N₄). Alternatively, the semiconductor may comprise zinc sulfide (ZnS), zinc selenide (ZnSe), gallium arsenide (GaAs). Metals comprise aluminum (Al), silver (Ag), magnesium (Mg), lithium (Li), or calcium (Ca).

Color filters comprising 140R, 140G, and 140G are subsequently formed on the micro-cavity layers 150a and 150b. The color filters 140R, 140G, and 140G may comprise organic materials formed by dyeing, pigment dispersion, printing, and electrochemical deposition.

Referring to FIG. 2C, the first substrate 110 and the second substrate 180 are assembled opposing each other such that the white OLED element directly contacts the color filters 140R, 140G, and 140G. The peripheral region of the first substrate

110 and the second substrate **180** is sealed by sealer **190**. Alternatively, the first substrate **110** and the second substrate **180** can be assembled in a frame.

According to an embodiment of the invention, a white light emitted by the OLED element sequentially passes through the color filters **140R**, **140G**, and **140B** and the micro-cavity layers **150a** and **150b**. Composition and reflection index can be varied according to light passing through the color filters **140R**, **140G**, and **140B**, to optimize color saturation.

From the fabrication point, of view, a high fabrication temperature process should occur prior to a low fabrication temperature process. Therefore, inorganic micro-cavity layers **150a** and **150b** are formed on the second substrate **180** at high temperature. The organic color filters **140R**, **140G**, and **140B** are sequentially formed on the micro-cavity layers **150a** and **150b** at low temperature. Moreover, the micro-cavity layers **150a** and **150b** the color filters **114R**, **140G**, and **140B** can be formed using a single lithographic process, thereby reducing fabrication costs.

FIGS. 3A-3C are cross sections of another embodiment of a method of fabricating an organic light emitting diode (OLED) device. Referring to FIG. 3A, micro-cavity layers **250a** and **250ba** are formed on a first substrate **220**, comprising a transparent substrate such as glass or a thin film transistor (TFT) array substrate. Micro-cavity layers **250a** and **250b** may comprise one or more materials with different refraction indices, such as oxides, nitrides, semiconductors, metals, or combination thereof. Exemplary oxides include silicon oxide (SiO₂), titanium oxide (TiO₂), tantalum oxide (Ta₂O₅), tin oxide (SnO₂), indium tin oxide (ITO), indium zinc oxide (IZO), or zinc oxide (ZnO). Nitrides may comprise silicon nitride (Si₃N₄). Alternatively, semiconductor may comprise zinc sulfide (ZnS), zinc selenide (ZnSe), gallium arsenide (GaAs). Metals comprise aluminum (Al), silver (Ag), magnesium (Mg), lithium (Li), or calcium (Ca).

Referring to FIG. 3B, color filters comprising **240R**, **240G**, and **240G** are subsequently formed on the micro-cavity layers **250a** and **250b**. The color filters **240R**, **240G**, and **240G** may comprise organic material formed by dying, pigment dispersion, printing, and electrochemical deposition.

Referring to FIG. 3C, a white OLED element **220** is formed on the color filters **240R**, **240G**, and **240G**. The white OLED element **220** comprises a first electrode **228**, an organic light emitting structure **225**, and a second electrode **222**. The white OLED element **220**, preferably a bottom emission OLED, emitting light toward an observer in the direction indicated by arrow *v*, emits spectrums comprising red (R), green (G), and blue (B) colors.

The first electrode **228** such as an anode is an electrode for hole injection, preferably comprising indium tin oxide (ITO) indium zinc oxide (IZO) silver (Ag), or other high work function material.

The organic light emitting structure **225** may preferably comprise an electron transport layer (ETL), an organic light emitting layer, and a hole transport layer (HTL). The organic light emitting layer **125** can be oligomer, polymer, or organic metallic complexes.

A second electrode **222**, such as a cathode, is a metal electrode for electron injection, preferably comprising, calcium (Ca), magnesium (Mg), aluminum (Al), or other low work function material. Alternatively, the second electrode

may comprise Ca—Al dual layer, Mg—Ag dual layer, LiF—Al dual layer or Mg—Ag alloy or stacks comprising ITO layer and electrodes thereof.

According to an embodiment of the invention, a white light emitted by the OLED element **220** sequentially passes through the color filters **240R**, **240G**, and **240B** and the micro-cavity layers **250a** and **250b**. The composition and reflection index can be varied according to light passing through the color filters **240R**, **240G**, and **240B**, to optimize color saturation.

From the fabrication point of view, a high fabrication temperature process should occur prior to a low fabrication temperature process. Therefore, inorganic micro-cavity layers **250a** and **250b** are formed on the second substrate **180** at high temperature. The organic color filters **140R**, **140G**, and **140B** and organic light emitting structure **225** are sequentially formed on the micro-cavity layers **250a** and **250b** at low temperature. Moreover, the micro-cavity layers, **250a** and **250b** and the color filters **240R**, **240G**, and **240B** can be formed using a single lithographic process, thereby reducing fabrication costs.

While the invention has been described by way of example and in terms of preferred embodiment, it is to be understood that the invention is not limited thereto. On the contrary, it is intended to cover various modifications and similar arrangements as would be apparent to those skilled in the art. Therefore, the scope of the appended claims should be accorded the broadest interpretation so as to encompass all such modifications and similar arrangements.

What is claimed is:

1. A method for fabricating an organic light emitting diode (OLED) display, comprising:

forming a white light OLED element on a first substrate; forming at least one micro-cavity layer on a second substrate;

forming a color filter on the at least one micro-cavity layer; and

assembling the first substrate and the second substrate opposing each other, whereby a white light emitted by the OLED element sequentially passes through the color filter and the at least one micro-cavity layer.

2. The method as claimed in claim 1, wherein the white light OLED element comprises a top emission OLED element.

3. The method as claimed in claim 1, wherein the white light emitted by the OLED element is comprised of red, green, and blue light.

4. The method as claimed in claim 1, wherein the at least one micro-cavity layer has one or more different refraction indices.

5. The method as claimed in claim 1, wherein the at least one micro-cavity layer comprises oxide, nitride, semiconductor, metal, or combinations thereof.

6. The method as claimed in claim 5, wherein the oxide comprises SiO₂, TiO₂, Ta₂O₅, SnO₂, indium tin oxide (ITO), indium zinc oxide (IZO), or ZnO.

7. The method as claimed in claim 5, wherein the nitride comprises Si₃N₄.

8. The method as claimed in claim 5, wherein the semiconductor comprises ZnS, ZnSe, or GaAs.

9. The method as claimed in claim 5, wherein the metal comprises Al, Ag, Mg, Li, or Ca.

* * * * *

专利名称(译)	制造电致发光显示器的方法		
公开(公告)号	US7416917	公开(公告)日	2008-08-26
申请号	US11/268847	申请日	2005-11-08
[标]申请(专利权)人(译)	友达光电股份有限公司		
申请(专利权)人(译)	友达光电.		
当前申请(专利权)人(译)	友达光电.		
[标]发明人	KO CHUNG WEN		
发明人	KO, CHUNG-WEN		
IPC分类号	H01L51/40 H01L21/00 H01L21/338		
CPC分类号	H01L27/322 H01L51/5265 H01L51/5036 H01L51/56 H01L51/5237 H01L51/524		
优先权	094107672 2005-03-14 TW		
其他公开文献	US20060220008A1		
外部链接	Espacenet USPTO		

摘要(译)

一种制造有机发光二极管 (OLED) 显示器的方法。在第一基板上形成白光OLED元件。在第二衬底上形成微腔层。在微腔层上形成滤色器。组装第一和第二基板，其中白色OLED元件的光穿过滤色器和微腔层。

